

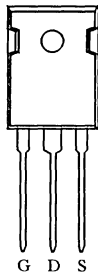
Siliconix

### N-Channel Enhancement-Mode Transistor

#### Product Summary

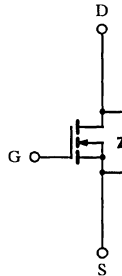
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.014	70

TO-247AD



Top View

DRAIN connected to TAB



N-Channel MOSFET

#### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	70
		$T_C = 100^\circ\text{C}$	48
Pulsed Drain Current	$I_{DM}$	280	A
Avalanche Current <sup>a</sup>	$I_{AR}$	70	
Repetitive Avalanche Energy	$E_{AR}$	$L = 0.1 \text{ mH}$	245
Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	150
		$T_C = 100^\circ\text{C}$	60
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Lead Temperature ( $1/16''$ from case for 10 sec.)	$T_L$	300	

#### Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient	$R_{thJA}$		40	$^\circ\text{C}/\text{W}$
Junction-to-Case	$R_{thJC}$		0.83	
Case-to-Sink	$R_{thCS}$	0.35		

Notes:

a. Duty cycle  $\leq 1\%$

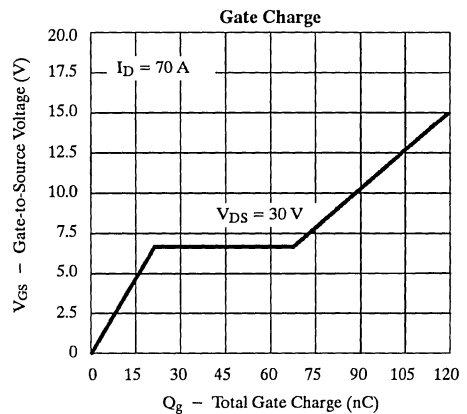
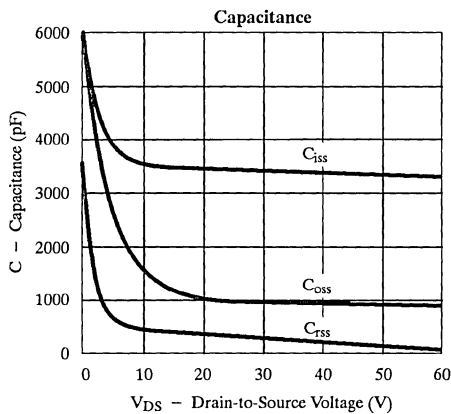
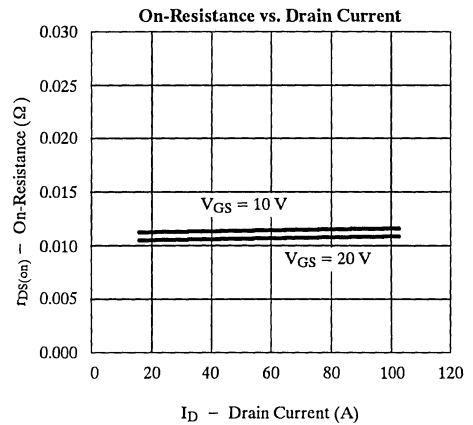
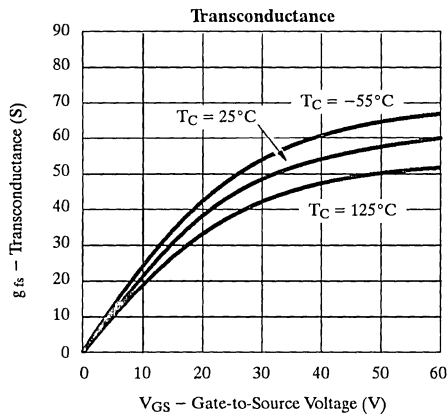
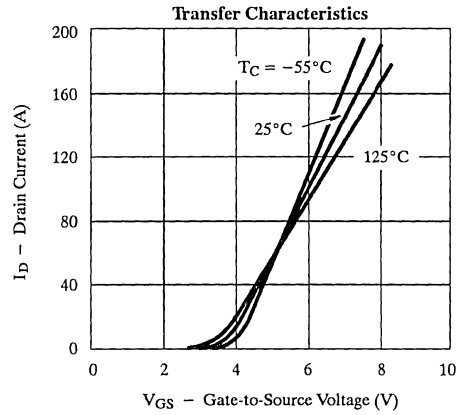
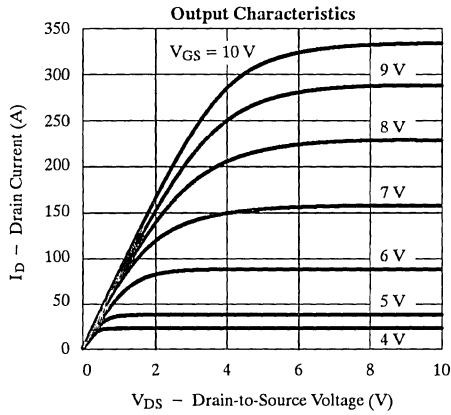
### Specifications ( $T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\ \text{mA}$	2.0	3.0	4.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			$\pm 500$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48\ \text{V}, V_{GS} = 0\ \text{V}$			25	$\mu\text{A}$
		$V_{DS} = 48\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 125^\circ\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 10\ \text{V}, V_{GS} = 10\ \text{V}$	70			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 35\ \text{A}$		0.012	0.014	$\Omega$
		$V_{GS} = 10\ \text{V}, I_D = 35\ \text{A}, T_J = 125^\circ\text{C}$		0.020	0.023	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\ \text{V}, I_D = 35\ \text{A}$	30	50		S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\ \text{V}, V_{DS} = 25\ \text{V}, f = 1\ \text{MHz}$		3450		pF
Output Capacitance	$C_{oss}$			1000		
Reverse Transfer Capacitance	$C_{rss}$			230		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 70\ \text{A}$		95	130	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			22		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			44		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\ \text{V}, R_L = 0.39\ \Omega$ $I_D = 70\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 2.5\ \Omega$		15	30	ns
Rise Time <sup>c</sup>	$t_r$			130	180	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			50	100	
Fall Time <sup>c</sup>	$t_f$			20	50	
<b>Source-Drain Diode Ratings and Characteristics (<math>T_C = 25^\circ\text{C}</math>)</b>						
Continuous Current	$I_S$				70	A
Pulsed Current	$I_{SM}$				280	
Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 70\ \text{A}, V_{GS} = 0\ \text{V}$		1.0	1.8	V
Reverse Recovery Time	$t_{rr}$	$I_F = 70\ \text{A}, di_F/dt = 100\ \text{A}/\mu\text{s}$		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$				9	A
Reverse Recovery Charge	$Q_{rr}$				0.6	$\mu\text{C}$

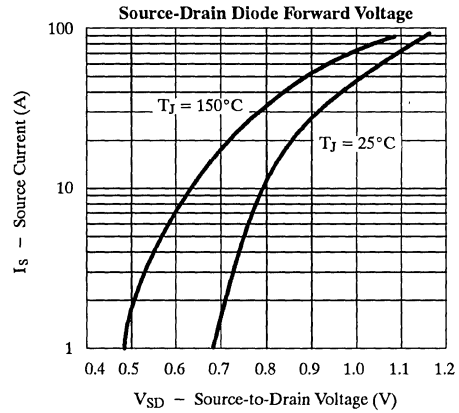
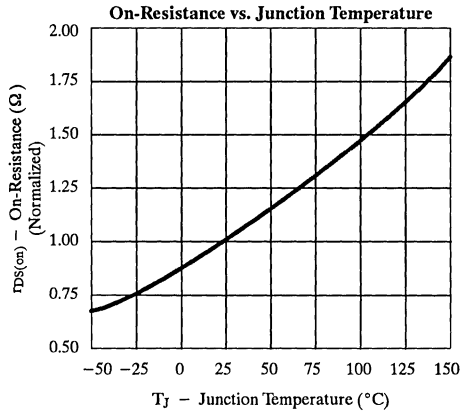
**Notes:**

- For design aid only; not subject to production testing.
- Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

### Typical Characteristics (25°C Unless Otherwise Noted)



### Typical Characteristics (25°C Unless Otherwise Noted)



### Thermal Ratings

